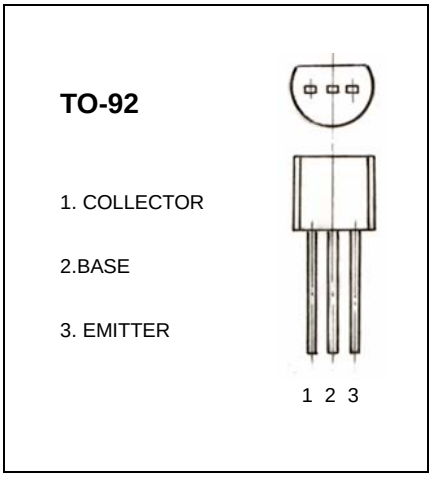
深圳市晶泰源电子有限公司

BC337/BC338 TRANSISTOR (NPN)

FEATURES

Power dissipation



MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter		Value	Units
V_{CBO}	Collector-Base Voltage	**BC337**	50	V
		BC338	30	
V_{CEO}	Collector-Emitter Voltage	**BC337**	45	V
		BC338	25	
V_{EBO}	Emitter-Base Voltage		5	V
I_C	Collector Current -Continuous		800	mA
P_D	Total Device Dissipation		625	mW
T_j	Junction Temperature		150	℃
T_{stg}	Storage Temperature		-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	I_C= 100uA, I_E=0				
BC337			50			V
BC338			30			V
Collector-emitter breakdown voltage	V_{CEO}	I_C= 10mA , I_B=0				
BC337			45			V
BC338			25			V
Emitter-base breakdown voltage	V_{EBO}	I_E= 10uA, I_C=0	5			V
Collector cut-off current BC337	I_{CBO}	V_{CB}= 45V, I_E=0			0.1	uA
BC338		V_{CB}= 25V, I_E=0			0.1	
Collector cut-off current BC337	I_{CEO}	V_{CE}= 40V, I_B=0			0.2	uA
BC338		V_{CE}= 20V, I_B=0			0.2	
Emitter cut-off current	I_{EBO}	V_{EB}= 4 V, I_C=0			0.1	uA
BC337/BC338	$h_{FE(1)}$	V_{CE}=1V, I_C= 100mA	100		630	
BC337-16/BC338-16			100		250	
BC337-25/BC338-25			160		400	
BC337-40/BC338-40			250		630	
DC current gain	$h_{FE(2)}$	V_{CE}=1V, I_C= 300mA	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500mA, I_B= 50mA			0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= 500mA, I_B=50mA			1.2	V
Base-emitter voltage	V_{BE}	V_{CE}=1V, I_C= 300mA			1.2	V
Transition frequency	f_T	V_{CE}= 5V, I_C= 10mA f = 100MHz	210			MHz
Collector Output Capacitance	Cob	V_{CB}=10V,I_E=0 f=1MHZ		15		pF

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